



40V +175°C N-CHANNEL ENHANCEMENT MODE MOSFET

Product Summary

BV _{DSS}	R _{DS(ON)}	I _D T _C = +25°C	
40V	$4.0 \text{m}\Omega$ @ $V_{GS} = 10V$	150A	

Description

This new generation Enhancement Mode MOSFET is designed to minimize $R_{DS(ON)}$ and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

Applications

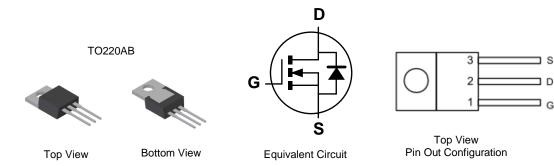
- Motor Control
- Backlighting
- DC-DC Converters
- Power Management Functions

Features

- Low Input Capacitance
- Low Input/Output Leakage
- Lead-Free Finish; RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability
- An Automotive-Compliant Part is Available Under Separate Datasheet (<u>DMNH4005SCTQ</u>)

Mechanical Data

- Case: TO220AB
- Case Material: Molded Plastic, "Green" Molding Compound, UL Flammability Classification Rating 94V-0
- Terminals: Matte Tin Finish Annealed over Copper Leadframe.
 Solderable per MIL-STD-202, Method 208 ⁽³⁾
- Terminal Connections: See Diagram Below
- Weight: 1.85 grams (Approximate)



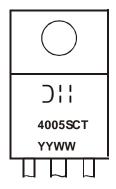
Ordering Information (Note 4)

1			
	Part Number	Case	Packaging
	DMNH4005SCT	TO220AB	50 Pieces/Tube

Notes:

- 1. EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant. All applicable RoHS exemptions applied.
- See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

Marking Information



Oll = Manufacturer's Marking
4005SCT = Product Type Marking Code
YYWW = Date Code Marking
YY = Last Two Digits of Year (ex: 16 = 2016)
WW = Week (01 to 53)



Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit		
Drain-Source Voltage	V_{DSS}	40	V		
Gate-Source Voltage	V_{GSS}	20	V		
Continuous Drain Current V _{GS} = 10V	Steady State	$T_{C} = +25^{\circ}C$ $T_{C} = +100^{\circ}C$	I _D	150 100	А
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%)	I _{DM}	90	Α		
Maximum Continuous Body Diode Forward Current (Note 5)			Is	80	Α
Avalanche Current (Note 6) L=1mH			I _{AS}	30	Α
Avalanche Energy (Note 6) L=1mH			E _{AS}	500	mJ

Thermal Characteristics

Characteristic			Value	Unit	
Dower Discipation	$T_C = +25^{\circ}C$)	165	W	
Power Dissipation	$T_{C} = +70^{\circ}C$	P _D	100	VV	
Thermal Resistance, Junction to Case		$R_{\theta JC}$	0.9	°C/W	
Operating and Storage Temperature Range		T _J , T _{STG}	-55 to +175	°C	

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

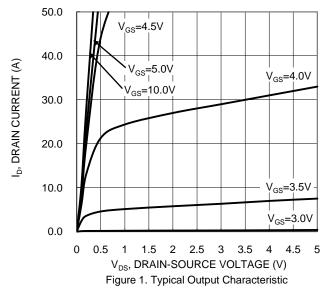
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 7)							
Drain-Source Breakdown Voltage	BV _{DSS}	40	_	_	V	$V_{GS} = 0V, I_D = 250\mu A$	
Zero Gate Voltage Drain Current	I _{DSS}	_	_	1	μA	$V_{DS} = 32V, V_{GS} = 0V$	
Gate-Source Leakage	IGSS	_	_	±100	nA	$V_{GS} = \pm 16V, V_{DS} = 0V$	
ON CHARACTERISTICS (Note 7)							
Gate Threshold Voltage	V _{GS(TH)}	1	_	3	V	$V_{DS} = V_{GS}$, $I_D = 250\mu A$	
Static Drain-Source On-Resistance	R _{DS(ON)}	_	3.4	4.0	mΩ	$V_{GS} = 10V, I_D = 20A$	
Diode Forward Voltage	V_{SD}	_	_	1.2	V	$V_{GS} = 0V, I_{S} = 1A$	
DYNAMIC CHARACTERISTICS (Note 8)							
Input Capacitance	C _{iss}	_	2846	_		201/11/	
Output Capacitance	Coss	_	742		pF	$V_{DS} = 20V, V_{GS} = 0V$ f = 1.0MHz	
Reverse Transfer Capacitance	C _{rss}	_	242	_		I = 1.0IVII IZ	
Gate Resistance	Rg	_	1.9	_	Ω	$V_{DS} = 0V, V_{GS} = 0V, f = 1.0MHz$	
Total Gate Charge (V _{GS} = 10V)	Qg	_	48	_		V _{DD} = 20V, I _D = 20A	
Total Gate Charge (V _{GS} = 4.5V)	Q_g	_	23	_	nC		
Gate-Source Charge	Qgs	_	9.5		liC		
Gate-Drain Charge	Q_{gd}	_	11.5	_			
Turn-On Delay Time	t _{D(ON)}	_	6.6			$V_{DD} = 20V, V_{GS} = 10V,$ $R_G = 1\Omega, I_D = 20A$	
Turn-On Rise Time	t _R	_	12.1	_			
Turn-Off Delay Time	t _{D(OFF)}	_	18.3	_	ns		
Turn-Off Fall Time	t _F	_	4.9	_			
Reverse Recovery Time	t _{RR}		29		ns	454 4:/44 4004/40	
Reverse Recovery Charge	Q _{RR}	_	24	_	nC	$I_F = 15A$, di/dt = 100A/ μ s	

5. Device mounted on FR-4 PC board, with minimum recommended pad layout, single sided.

I_{AS} and E_{AS} ratings are based on low frequency and duty cycles to keep T_J = +25°C.
 Short duration pulse test used to minimize self-heating effect.
 Guaranteed by design. Not subject to product testing.



DMNH4005SCT



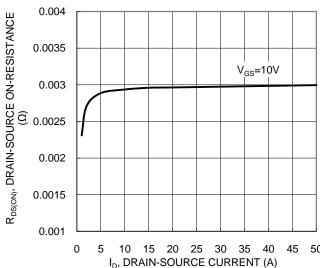


Figure 3. Typical On-Resistance vs. Drain Current and Gate Voltage

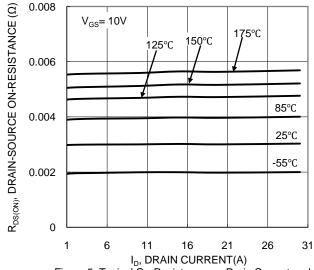
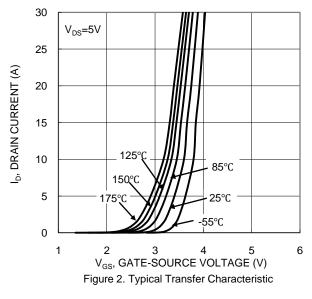
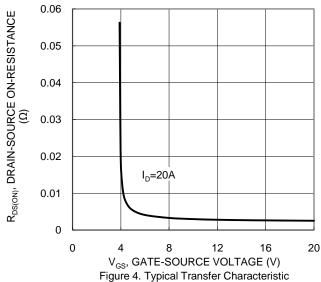


Figure 5. Typical On-Resistance vs. Drain Current and Junction Temperature





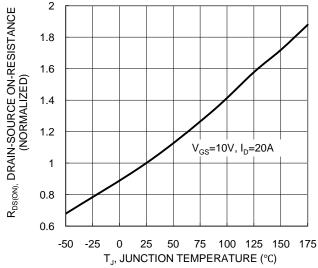
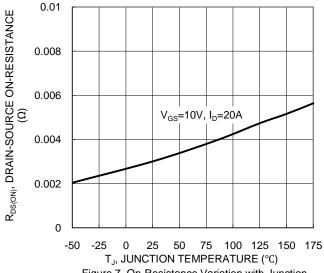
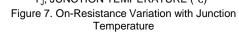


Figure 6. On-Resistance Variation with Junction Temperature







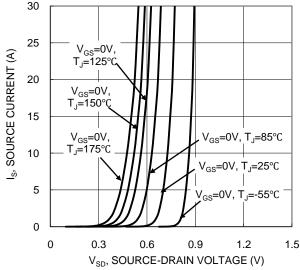
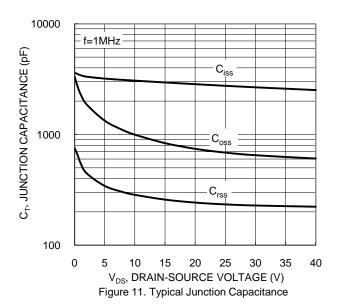


Figure 9. Diode Forward Voltage vs. Current



4 $V_{GS(TH)_{\rm i}}$ GATE THRESHOLD VOLTAGE (V) 3.5 3 I_D=1mA 2.5 2 $I_D = 250 \mu A$ 1.5 0.5 0 -50 -25 25 50 75 100 125 150 175 0 T_J, JUNCTION TEMPERATURE (°C)

Figure 8. Gate Threshold Variation vs. Junction Temperature

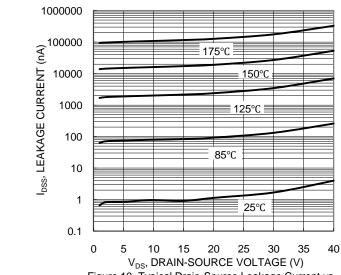


Figure 10. Typical Drain-Source Leakage Current vs. Voltage

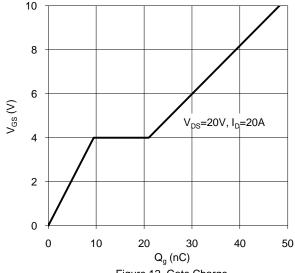
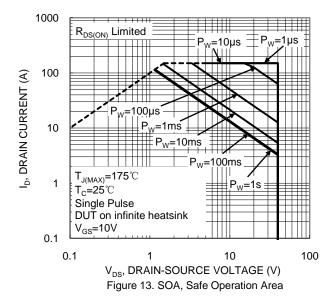


Figure 12. Gate Charge





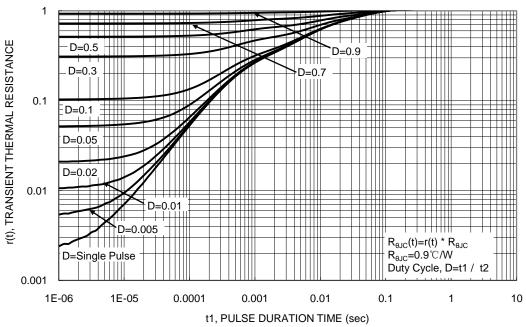


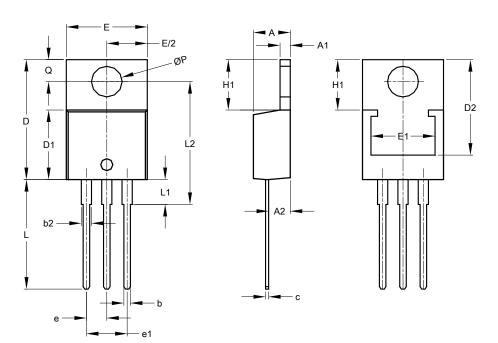
Figure 14. Transient Thermal Resistance



Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

TO220AB



TO220AB						
Dim	Min	Max	Тур			
Α	3.56	4.82	-			
A1	0.51	1.39	-			
A2	2.04	2.92	-			
b	0.39	1.01	0.81			
b2	1.15	1.77	1.24			
С	0.356	0.61	-			
D	14.22	16.51	-			
D1	8.39	9.01	-			
D2	11.45	12.87	-			
е	-	-	2.54			
e1	-	-	5.08			
Е	9.66	10.66	-			
E1	6.86	8.89	-			
H1	5.85	6.85	-			
L	12.70	14.73	-			
L1	-	6.35	-			
L2	15.80	16.20	16.00			
Р	3.54	4.08	-			
Q	2.54	3.42	-			
All Dimensions in mm						



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7 of 7

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